

providing a capacitor having a first plate, a dielectric over the first plate, and a second plate over the dielectric, the second plate including first and second conductive layers;

exposing said first conductive layer to a material selected from the group consisting of phosphine, and methylsilane to reduce an ability of the first conductive layer to associate with oxygen; and

E1 forming the second conductive layer on the first conductive layer, the second conductive layer being formed after the first conductive layer has been exposed to the material from the group.

894. (Twice Amended) A method of treating a semiconductor device, comprising:

E2 providing a capacitor having a first plate, a dielectric on the first plate, a first conductive layer on the dielectric with the first conductive layer having an ability to associate with oxygen, an oxide layer on the first conductive layer, and a second conductive layer on the oxide layer;

exposing the capacitor to a thermal process; and

prior to exposure to the thermal process and prior to forming the second conductive layer on the first conductive layer, exposing the first conductive layer to a material selected from the group consisting of phosphine, and methylsilane to reduce an amount of oxygen associated with the first conductive material during formation of the second conductive layer and reduce a thickness of the oxide layer subsequently formed between the first and second conductive layers during exposure of the capacitor to the thermal process.

Please add new claims 106-110 as follows:

E3 3-106. (New) The method of claim 91 wherein the dielectric comprises tantalum pentoxide.